SLD1133VL

650nm Index-Guided Red Laser Diode

Description

The SLD1133VL is an index-guided red laser diode designed for DVD systems. For bar code scanners, its wavelength (650nm Typ.) is 20nm shorter than that of the current device.

Features

- Small astigmatism (7µm typ.)
- Low operating current (60mA typ.)
- Small package (\$\phi 5.6mm)
- Single longitudinal mode

Applications

- DVD
- · Bar code scanner
- · Laser pointer

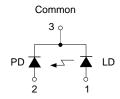
Structure

- AlGaInP quantum well structure laser diode
- PIN photo diode for optical power output monitor

Recommended Optical Power Output

5mW

Connection Diagram



M-274

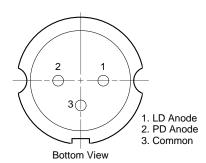
Absolute Maximum Ratings (Tc = 25°C)

 Optical power output 	Po		7	mW
 Reverse voltage 	V_R	LD	2	V
		PD	15	V

Operating temperature Topr –10 to +60 °C

Storage temperature Tstg -40 to +85 °C

Pin Configuration



Sony reserves the right to change products and specifications without prior notice. This information does not convey any license by any implication or otherwise under any patents or other right. Application circuits shown, if any, are typical examples illustrating the operation of the devices. Sony cannot assume responsibility for any problems arising out of the use of these circuits.

Electrical and Optical Characteristics (Tc = 25°C)

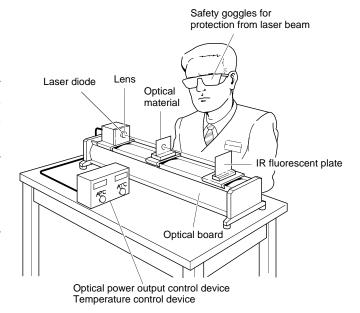
Tc: Case temperature	Tc:	Case	tem	peratur	е
----------------------	-----	------	-----	---------	---

Į.	tem	Symbol	Conditions	Min.	Тур.	Max.	Unit
Threshold cu	rrent	Ith			50	65	mA
Operating cur	rrent	lop	Po = 5mW		60	70	mA
Operating vol	ltage	Vop	Po = 5mW		2.3	2.8	V
Wavelength		λ	Po = 5mW	640	650	660	nm
Radiation	Perpendicular	θΤ	B 5 W	24	30	40	degree
angle	Parallel	θ//	Po = 5mW	6	8	12	degree
	Position	ΔΧ, ΔΥ, ΔΖ				±80	μm
Positional accuracy	Anglo	Δφ//	Po = 5mW			±2	degree
Aligie	Angle	△				±3	degree
Differential ef	ficiency	ηD	Po = 5mW	0.15	0.4	0.7	mW/mA
Astigmatism		As	Po = 5mW		7	15	μm
Monitor curre	nt	Imon	Po = 5mW, V _R = 5V	0.05	0.1	0.3	mA

Handling Precautions

(1) Eye protection against laser beams

The optical output of laser diodes ranges from several mW to 4W. However the optical power density of the laser beam at the diode chip reaches 1MW/cm². Unlike gas lasers, since laser diode beams are divergent, uncollimated laser diode beams are fairly safe at a laser diode. For observing laser beams, ALWAYS use safety goggles that block infrared rays. Usage of IR scopes, IR cameras and fluorescent plates is also recommended for monitoring laser beams safely.



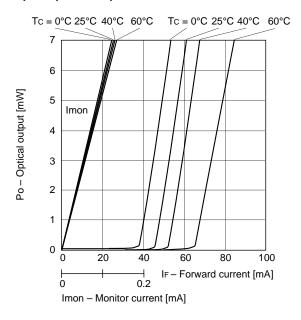
(2) Prevention of surge current and electrostatic discharge

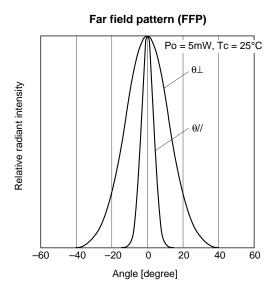
Laser diode is most sensitive to electrostatic discharge among semiconductors. When a large current is passed through the laser diode even for an extremely short time (in the order of nanosecond), the strong light emitted from the laser diode promotes deterioration and then laser diodes are destroyed. Therefore, note that the surge current should not flow the laser diode driving circuit from switches and others. Also, if the laser diode is handled carelessly, it may be destructed instantly because electrostatic discharge is easily applied by a human body. Be great careful about excess current and electrostatic discharge.

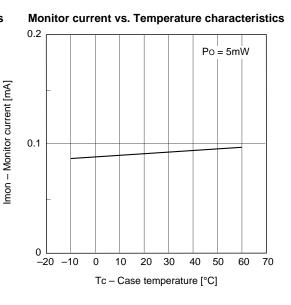


Example of Representative Characteristics

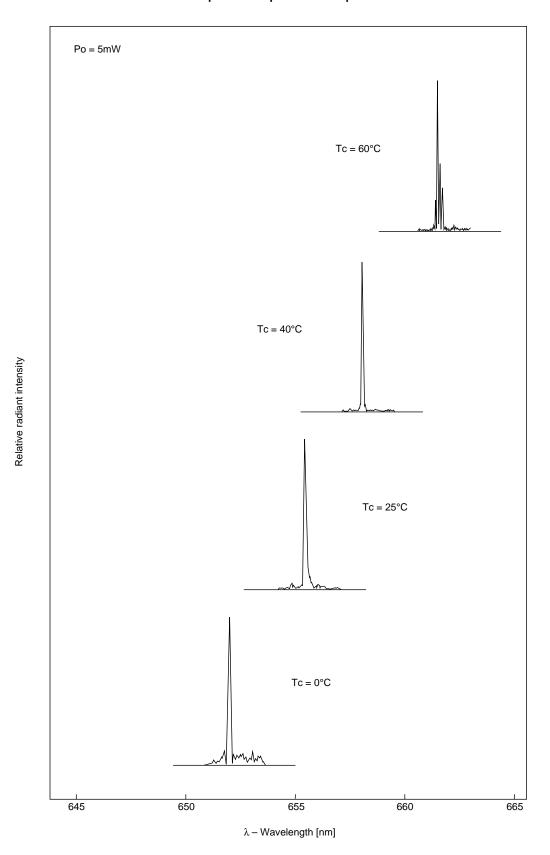
Optical power output vs. Forward current characteristics Optical power output vs. Monitor current characteristics



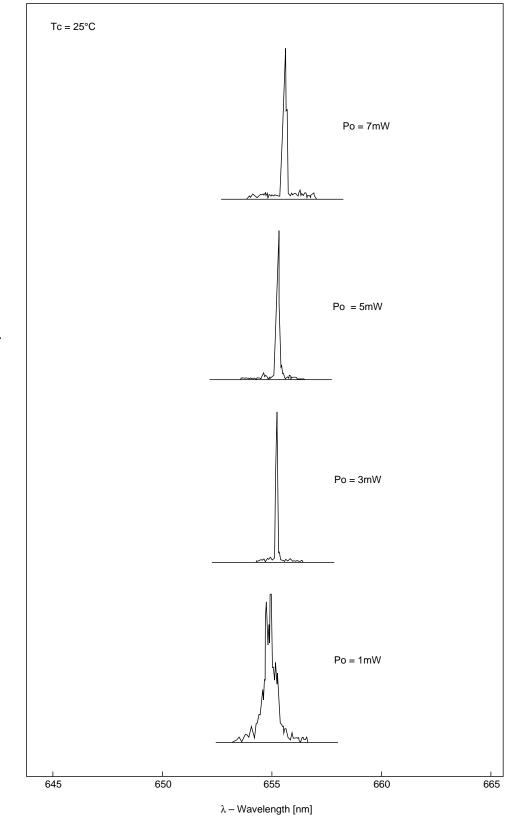




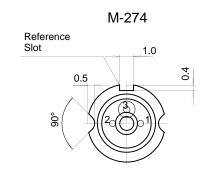
Temperature dependence of spectrum

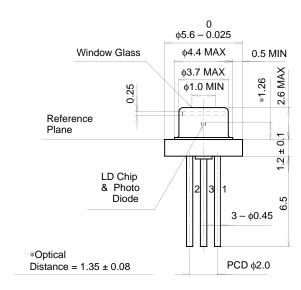


Power output dependence of spectrum



Package Outline Unit: mm





SONY CODE	M-274
EIAJ CODE	
JEDEC CODE	

PACKAGE WEIGHT 0.3g	
---------------------	--